

# SLD65R565SS / SLF65R565SS

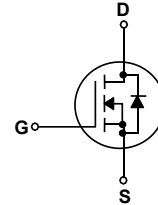
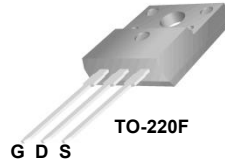
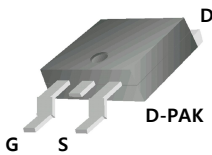
## 650V N-Channel MOSFET

### General Description

This Power MOSFET is produced using Maple semi's advanced planar stripe SuperJunction technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

### Features

- 8A, 650V,  $R_{DS(on)typ.} = 520m\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 12nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	SLD65R565SS	SLF65R565SS	Units
$V_{DSS}$	Drain-Source Voltage	650		V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	8		A
		5		A
$I_{DM}$	Drain Current - Pulsed (Note 1)	32		A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$		V
EAS	Single Pulsed Avalanche Energy (Note 2)	147		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	50		V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	66	29	W
		0.53	0.23	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

\* Drain current limited by maximum junction temperature.

### Thermal Characteristics

Symbol	Parameter	SLD65R565SS	SLF65R565SS	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.9	43	$^\circ\text{C}/\text{W}$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	-	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.0	62.5	$^\circ\text{C}/\text{W}$

**Electrical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	650	--	--	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 650\text{ V}, T_C = 125^\circ\text{C}$	--	0.8	-	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 4.0\text{ A}$	--	520	565	m $\Omega$
$R_g$	Gate Resistance	$V_{GS} = 0\text{ V}, V_{DS} = 0\text{ V}, F = 1\text{ MHz}$	--	5.5	--	$\Omega$

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	480	--	pF
$C_{oss}$	Output Capacitance		--	28	--	pF
$C_{rss}$	Reverse Transfer Capacitance		--	1.6	--	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}, I_D = 8\text{ A},$ $R_G = 25\text{ }\Omega, V_{GS} = 10\text{ V}$ (Note 4, 5)	--	11	--	ns
$t_r$	Turn-On Rise Time		--	27	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	23	--	ns
$t_f$	Turn-Off Fall Time		--	24	--	ns
$Q_g$	Total Gate Charge	$V_{DS} = 480\text{ V}, I_D = 8\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	12	--	nC
$Q_{gs}$	Gate-Source Charge		--	4.8	--	nC
$Q_{gd}$	Gate-Drain Charge		--	4.9	--	nC

**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	8	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	32	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 8\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 8\text{ A},$ $dI_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	215	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	1.8	--	$\mu\text{C}$
$I_{RRM}$	Reverse Recovery peak current	$V_{GS} = 0\text{ V}, I_S = 8\text{ A}, dI_F / dt = 100\text{ A}/\mu\text{s}$	-	16	-	A

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 79\text{ mH}, I_{AS} = 1.8\text{ A}, V_{DD} = 100\text{ V}, R_G = 25\text{ }\Omega,$  Starting  $T_J = 25^\circ\text{C}$
3. Pulse Test : Pulse width  $\leq 300\text{ }\mu\text{s},$  Duty cycle  $\leq 2\%$
4. Essentially independent of operating temperature

### Typical Characteristics

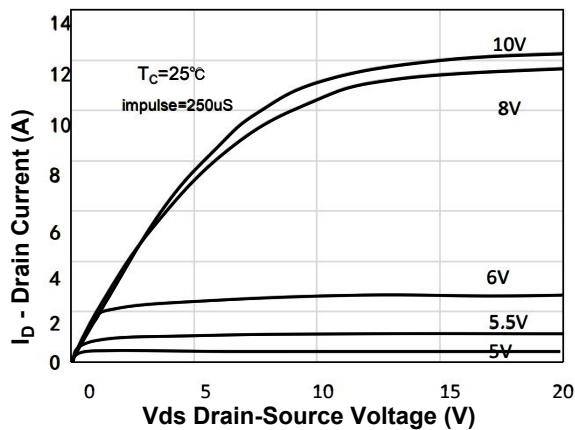


Figure 1. On-Region Characteristics

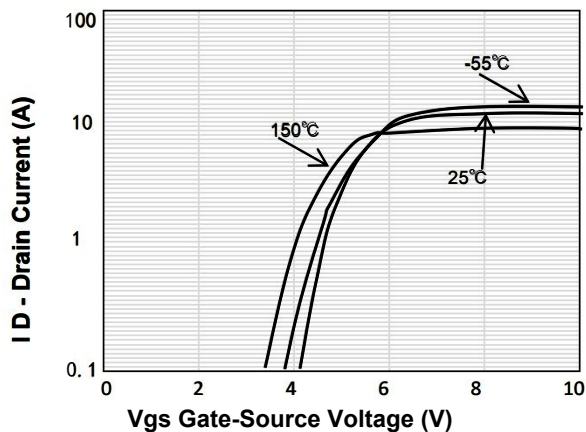


Figure 2. Transfer Characteristics

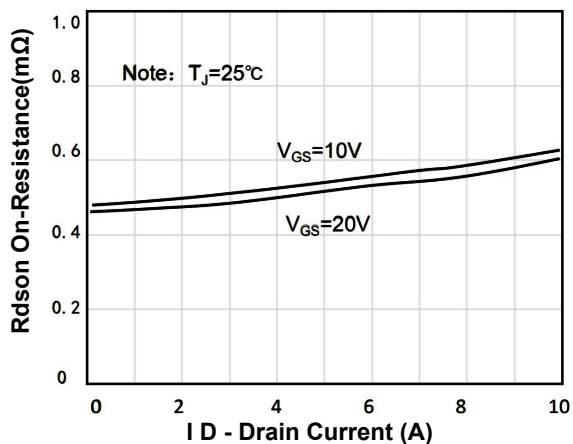


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

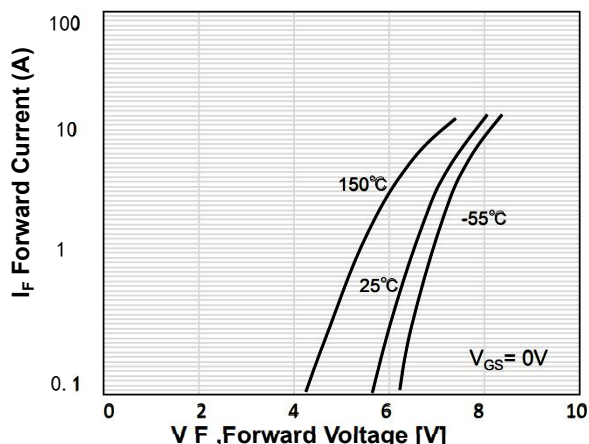


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

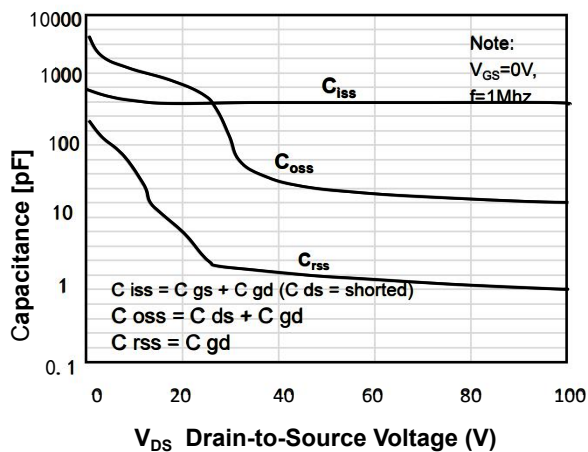


Figure 5. Capacitance Characteristics

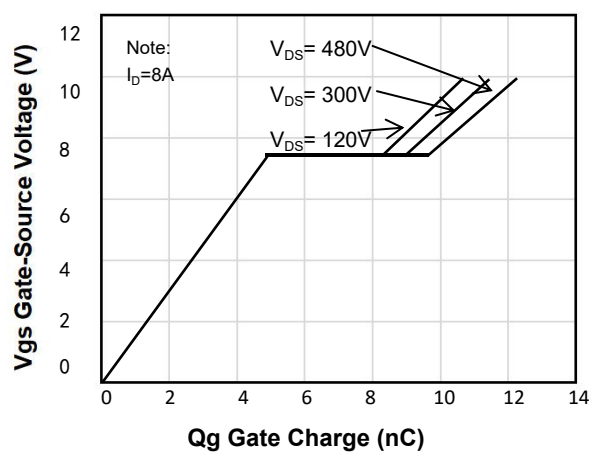


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

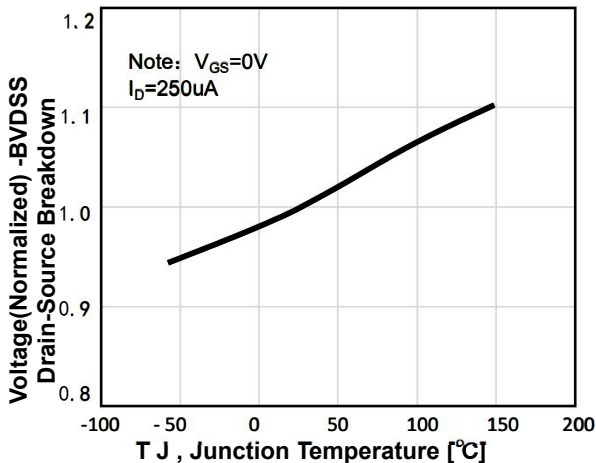


Figure 7. Breakdown Voltage Variation vs Temperature

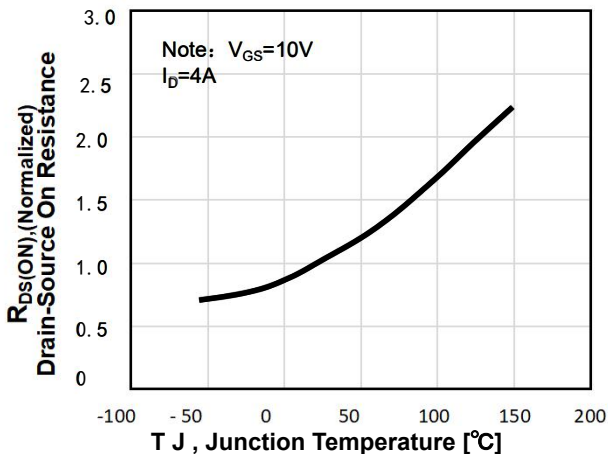


Figure 8. On-Resistance Variation vs Temperature

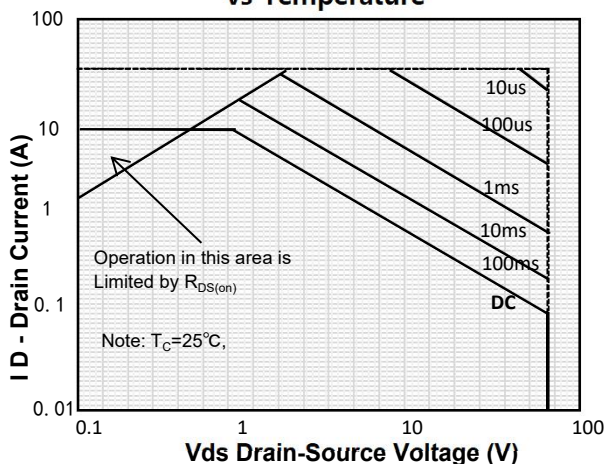


Figure 9-1. Maximum Safe Operating Area for SLD65R575SS

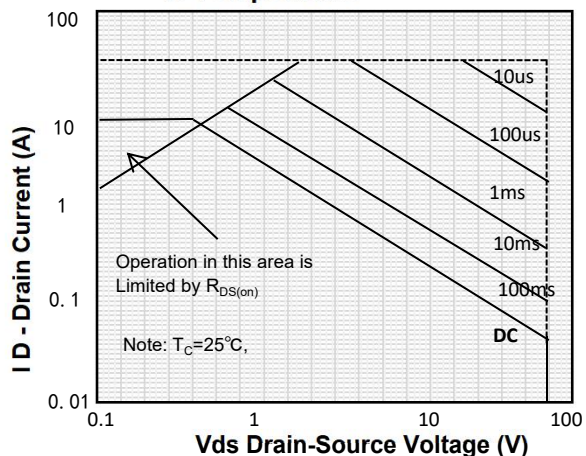


Figure 9-2. Maximum Safe Operating Area for SLF65R575SS

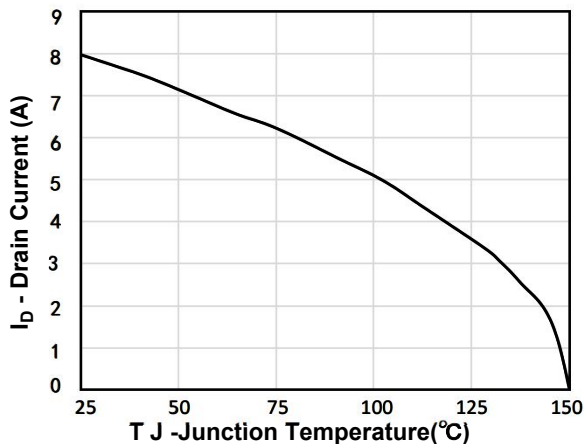


Figure 10. Maximum Drain Current vs Case Temperature

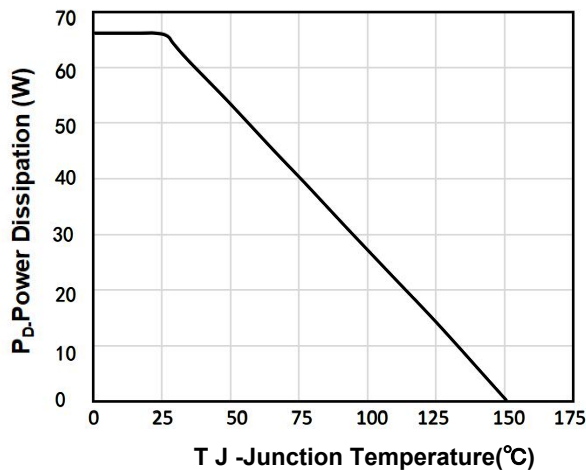
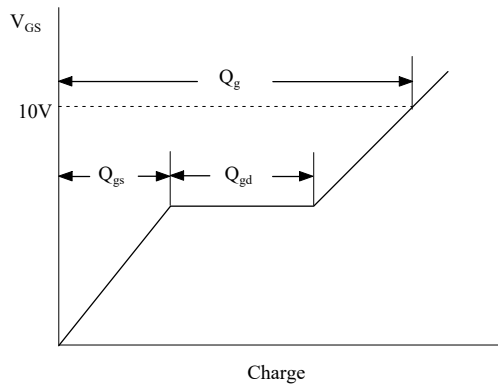
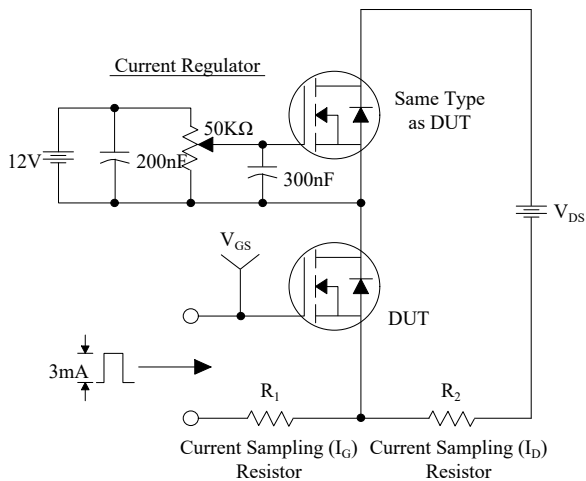
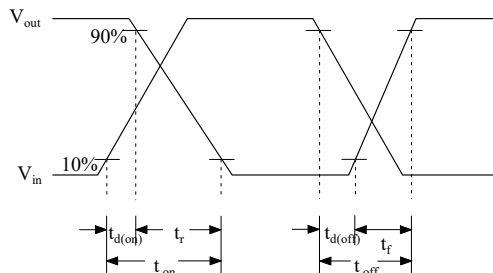
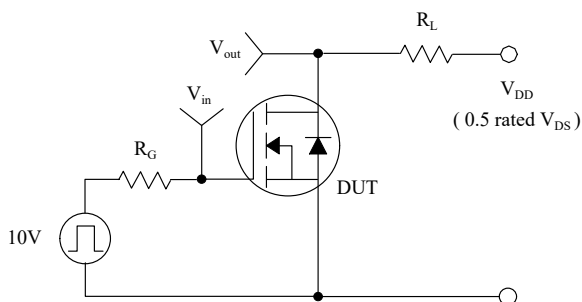


Figure 11. Power consumption varies with temperature

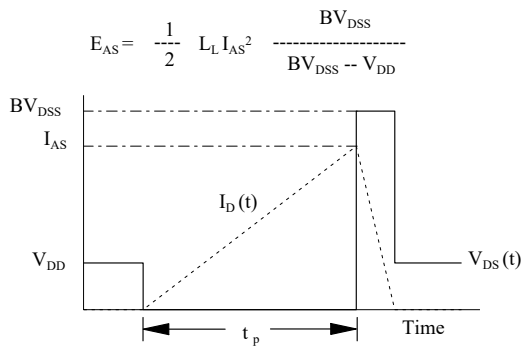
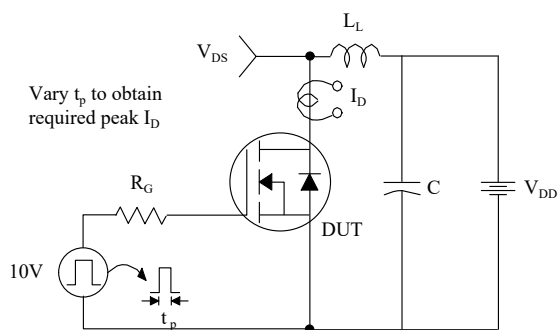
### Gate Charge Test Circuit & Waveform



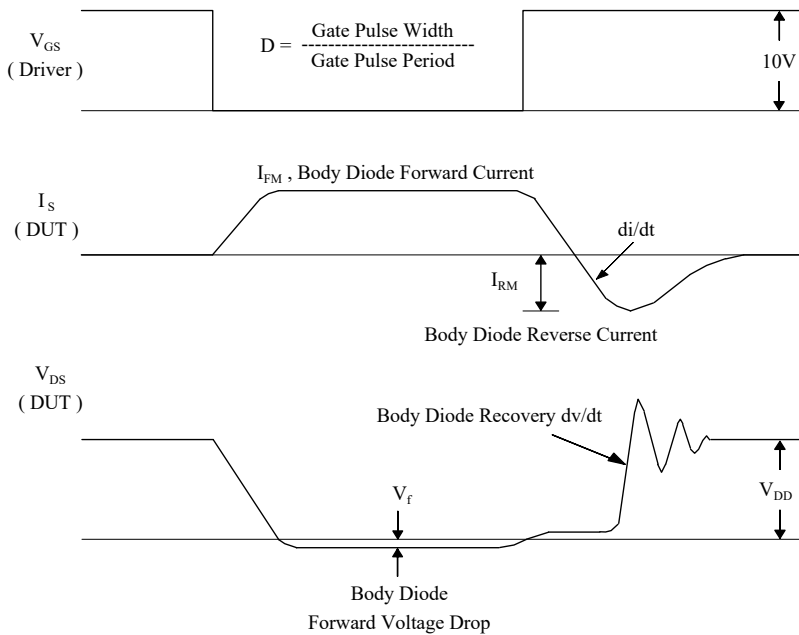
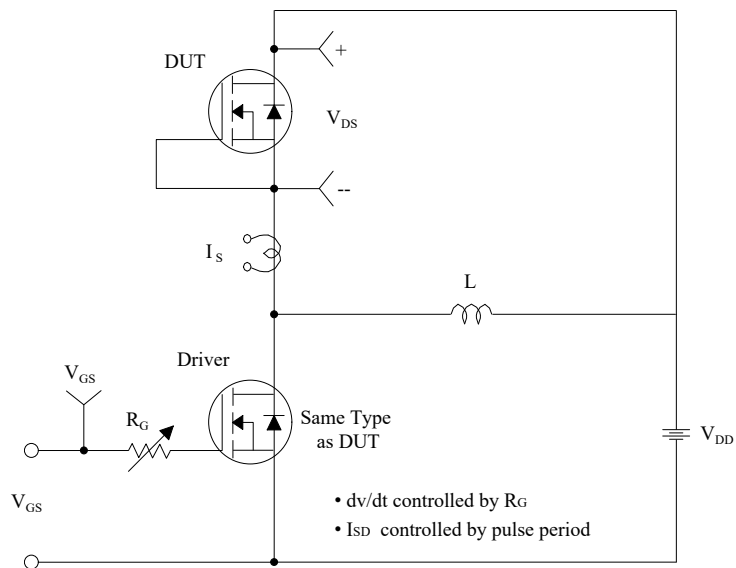
### Resistive Switching Test Circuit & Waveforms



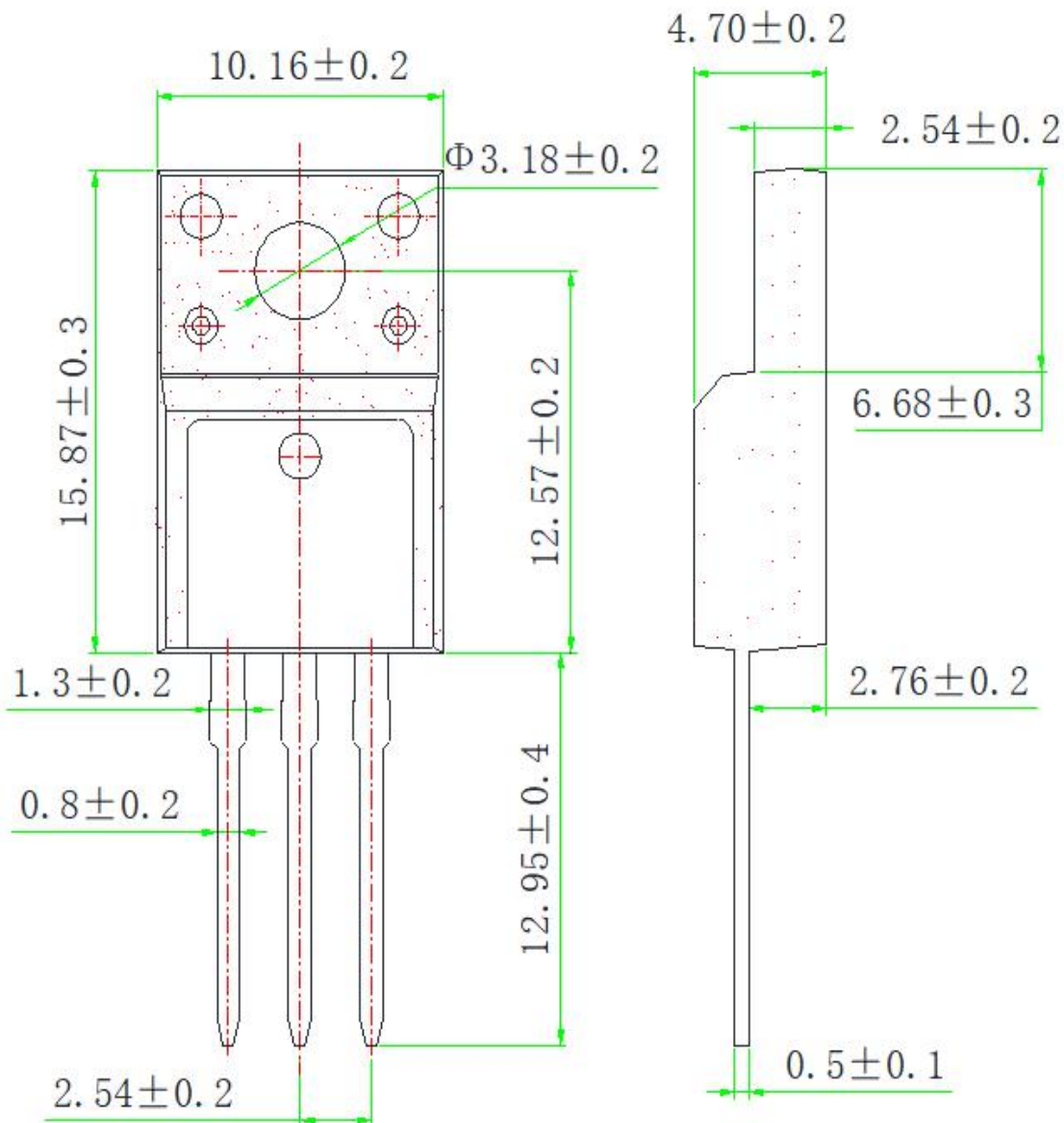
### Unclamped Inductive Switching Test Circuit & Waveforms



## Peak Diode Recovery dv/dt Test Circuit & Waveforms



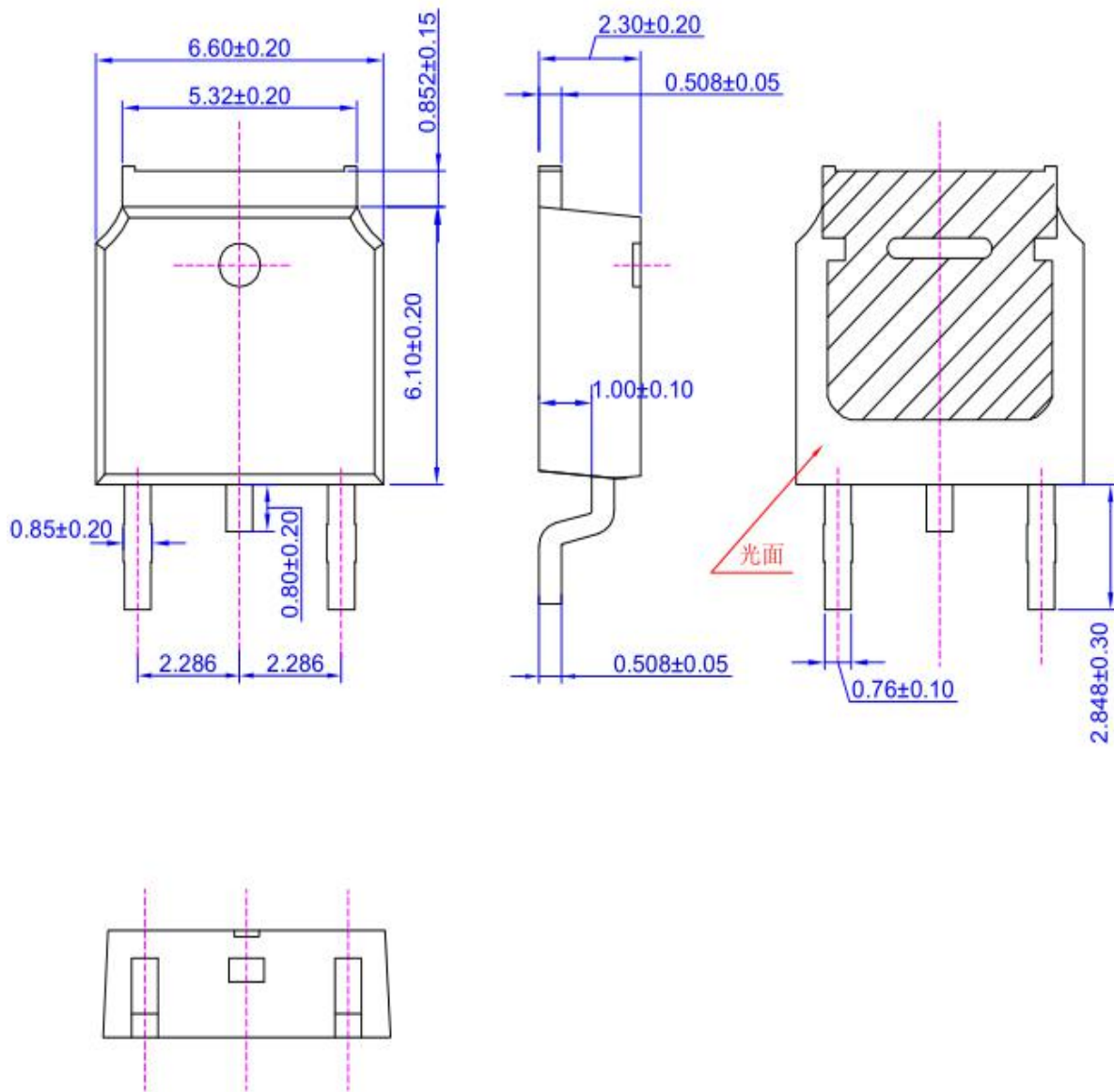
### TO-220F OUTLINE



**Note:**

- 1,Unit: millimeters
- 2,The tolerance not noted is  $\pm 0.15$ , and the unmarked fillet  $R_{max} = 0.25$

# TO-252 OUTLINE



**Note:**

- 1, Unit: millimeters
- 2, The tolerance not noted is  $\pm 0.15$ , and the unmarked fillet  $R_{max} = 0.25$